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Docket No.: M4065.0434/P434
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Ronald A. Weimer, et al.

Application No.: 09/805,911

Group Art Unit: 2823

Filed: March 15, 2001

Examiner: F. Toledo

For: USE OF ATOMIC OXYGEN PROCESS
FOR IMPROVED BARRIER LAYER

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AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 20, 2002 (Paper No. 5),
please amend the above-identified U.S. patent application as follows:

In the Specification

On pages 3 and 4, please replace paragraph [0006] with the following
paragraph:

A1 [0006] The insulating layer 24 (Figure 2) is typically composed of a
borophosphosilicate glass (BPSG) or a non-doped silicate glass (NSG), which is
formed over the gate stacks 30 and the source/drain regions 40 by deposition, for
example, and then undergoes a thermal treatment to facilitate the planarizing of the
insulating material. Since the thermal treatment of the insulating layer 24 typically
requires temperatures higher than 500°C, boron (B) and/or phosphorous (P)